

IN THE SPECIFICATION:

Replace the paragraph at lines 18-19 of page 3 with the following paragraph:

--FIG. 1 is a ~~front~~top view of a distributed feedback semiconductor laser according to a preferred embodiment of the present invention;--

Replace the first paragraph on page 4 with the following paragraph:

--Figs. 4 to ~~7~~8 are views for describing the manufacturing process of the distributed feedback semiconductor laser shown in FIG. 1.—

Replace the paragraph at lines 11-16 of page 4 with the following paragraph:

--FIG. 1 is a ~~front~~top view of a distributed feedback semiconductor laser according to a preferred embodiment of the present invention. FIG. 2 is a side sectional view taken along line A-A in the distributed feedback semiconductor laser of FIG. 1. The distributed feedback semiconductor laser includes a semiconductor substrate 110, upper and lower clad layers 120 and 160, a grating 130, a guide layer 140, an active layer 150, an upper electrode 170 and a lower electrode 180.—

Replace the paragraph at lines 7-8 of page 6 with the following paragraph:

--FIGs. 4 to ~~7~~8 are views for describing manufacturing process of the distributed feedback semiconductor laser shown in FIG. 1.--